



Form 1449 (Modified)  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No. UNTYP016 Applicant: Rinerson et al. Filing Date July 1, 2003	Application No.: 10/613,099  Group 2824
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#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
at	A	6,204,139	2001-03-20	Liu et al.	438	385	
	B	5,920,500	1999-07-06	Tehrani et al.	365	173	
	C	6,545,891	2003-04-08	Tringali et al.	365	51	
	D	6,504,753	2003-01-07	Scheuerlein et al.	365	175	
	E	6,483,736	2002-11-19	Johnson et al.	365	130	
	F	6,385,074	2002-05-07	Johnson et al.	365	103	
	G	6,351,406	2002-02-26	Johnson et al.	365	103	
	H	6,185,122	2001-02-06	Johnson et al.	365	103	
	I	6,034,882	2000-03-07	Johnson et al.	365	103	
	J	5,835,396	1998-11-10	Zhang	365	51	
at	K	4,442,507	1994-04-10	Roesner	365	100	

#### U.S. Published Patent Applications

Examiner Initial	No.	Document No.	Publication Date	Inventor
at	J	2002/0000597 A1	01/03/02	Okazawa
at	K	2001/0023992 A1	09/27/01	Doll

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
at	L	Beck, A. et al., "Reproducible switching effect in thin oxide films for memory applications", Applied Physics Letters, Vol. 77, No. 1, 3 July 2000, 139-141.
at	M	Rossel, C. et al., "Electrical current distribution across a metal-insulator-metal structure during bistable switching", Journal of Applied Physics, Vol. 90, No. 6, 15 September 2001, 2892-2898.
at	N	Watanabe, Y. et al., "Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped SrTiO <sub>3</sub> single crystals", Applied Physics Letters, Vol. 78, No. 23, 4 June 2001, 3738-3740.
Examiner <i>alson</i>		Date Considered 02/23/2004

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.